

In the claims:

Please amend the claims as follows:

Claim 1 (currently amended): A method for manufacturing a semiconductor device having at least one thin film ~~transistors~~ transistor, said method comprising the steps of:

 forming a semiconductor layer over a substrate;
 irradiating said semiconductor layer with a laser beam to crystallize said semiconductor layer; and

 forming source, drain and channel region of said thin film transistor within said semiconductor layer,

 wherein said laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source,

 wherein the irradiation of said semiconductor layer is conducted in such a manner that said semiconductor layer is scanned with said laser beam in parallel with a carrier flow direction in said channel region.

Claim 2 (currently amended): A method for manufacturing a semiconductor device having at least one thin film ~~transistors~~ transistor, said method comprising the steps of:

 forming a semiconductor layer over a substrate;
 irradiating said semiconductor layer with a linear laser beam to crystallize said semiconductor layer; and

 forming source, drain and channel region of said thin film transistor within said semiconductor layer,

 wherein said linear laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source,

 wherein the irradiation of said semiconductor layer is conducted in such a manner that said semiconductor layer is scanned with said linear laser beam in parallel with a carrier flow direction in said channel region.

Claims 3-8 (withdrawn).

Claim 9 (currently amended): A method of manufacturing a semiconductor device having at least one thin film transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate; and
irradiating said semiconductor layer with a linear laser beam to crystallize said semiconductor layer, while moving said substrate in a direction approximately perpendicular to a lengthy direction of said linear laser beam,
wherein said linear laser beam is a second harmonic component generated from a continuous oscillate continuously-oscillating light source.

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Claim 10 (currently amended): A method of manufacturing a semiconductor device having at least one thin film transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate;
irradiating said semiconductor layer with a laser beam to crystallize said semiconductor layer; and
 patterning the crystallized semiconductor layer to form an active layer of said thin film transistor,
wherein said laser beam is a second harmonic component generated from a continuous oscillate continuously-oscillating light source.

Claims 11-16 (withdrawn).

Claim 17 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein said semiconductor layer comprises amorphous silicon.

Claim 18 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein said semiconductor layer comprises silicon and germanium.

Claim 19 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains carbon at a concentration not higher than 5×10^{18} atoms/cm³.

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Claim 20 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains oxygen at a concentration not higher than 5×10^{19} atoms/cm³.

Claim 21-30 (withdrawn).
